

IRF7325

HEXFET® Power MOSFET

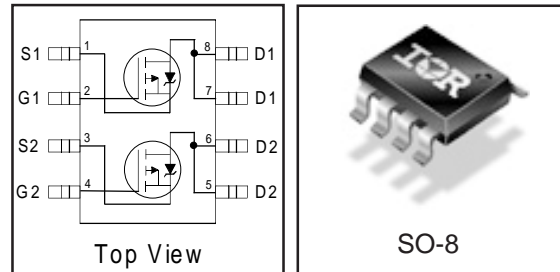
- Trench Technology
- Ultra Low On-Resistance
- Dual P-Channel MOSFET
- Low Profile (<1.8mm)
- Available in Tape & Reel

| V_{DSS} | $R_{DS(on)}$ max (m Ω) | I_D |
|-----------|--------------------------------|------------|
| -12V | 24@ $V_{GS} = -4.5V$ | $\pm 7.8A$ |
| | 33@ $V_{GS} = -2.5V$ | $\pm 6.2A$ |
| | 49@ $V_{GS} = -1.8V$ | $\pm 3.9A$ |

Description

New P-Channel HEXFET® power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infrared, or wave soldering techniques.



Absolute Maximum Ratings

| | Parameter | Max. | Units |
|--------------------------|--|--------------|----------------|
| V_{DS} | Drain- Source Voltage | -12 | V |
| $I_D @ T_A = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ -4.5V$ | -7.8 | A |
| $I_D @ T_A = 70^\circ C$ | Continuous Drain Current, $V_{GS} @ -4.5V$ | -6.2 | |
| I_{DM} | Pulsed Drain Current ① | -39 | |
| $P_D @ T_A = 25^\circ C$ | Power Dissipation ③ | 2.0 | W |
| $P_D @ T_A = 70^\circ C$ | Power Dissipation ③ | 1.3 | |
| | Linear Derating Factor | 16 | mW/ $^\circ C$ |
| V_{GS} | Gate-to-Source Voltage | ± 8.0 | V |
| T_J, T_{STG} | Junction and Storage Temperature Range | -55 to + 150 | $^\circ C$ |

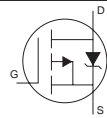
Thermal Resistance

| Symbol | Parameter | Typ. | Max. | Units |
|-----------------|------------------------|------|------|--------------|
| $R_{\theta JL}$ | Junction-to-Drain Lead | — | 20 | $^\circ C/W$ |
| $R_{\theta JA}$ | Junction-to-Ambient ③ | — | 62.5 | |

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---------------------------------|--------------------------------------|-------|-------|-------|---------------------|---|
| $V_{(BR)DSS}$ | Drain-to-Source Breakdown Voltage | -12 | — | — | V | $V_{GS} = 0V, I_D = -250\mu A$ |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | — | 0.007 | — | V/ $^\circ\text{C}$ | Reference to $25^\circ\text{C}, I_D = -1\text{mA}$ |
| $R_{DS(on)}$ | Static Drain-to-Source On-Resistance | — | — | 24 | m Ω | $V_{GS} = -4.5V, I_D = -7.8A$ ② |
| | | — | — | 33 | | $V_{GS} = -2.5V, I_D = -6.2A$ ② |
| | | — | — | 49 | | $V_{GS} = -1.8V, I_D = -3.9A$ ② |
| $V_{GS(th)}$ | Gate Threshold Voltage | -0.40 | — | -0.90 | V | $V_{DS} = V_{GS}, I_D = -250\mu A$ |
| g_{fs} | Forward Transconductance | 17 | — | — | S | $V_{DS} = -10V, I_D = -7.8A$ |
| I_{DSS} | Drain-to-Source Leakage Current | — | — | -1.0 | μA | $V_{DS} = -9.6V, V_{GS} = 0V$ |
| | | — | — | -25 | | $V_{DS} = -9.6V, V_{GS} = 0V, T_J = 70^\circ\text{C}$ |
| I_{GSS} | Gate-to-Source Forward Leakage | — | — | -100 | nA | $V_{GS} = -8.0V$ |
| | Gate-to-Source Reverse Leakage | — | — | 100 | | $V_{GS} = 8.0V$ |
| Q_g | Total Gate Charge | — | 22 | 33 | nC | $I_D = -7.8A$ |
| Q_{gs} | Gate-to-Source Charge | — | 5.0 | 7.5 | | $V_{DS} = -6.0V$ |
| Q_{gd} | Gate-to-Drain ("Miller") Charge | — | 4.7 | 7.0 | | $V_{GS} = -4.5V$ |
| $t_{d(on)}$ | Turn-On Delay Time | — | 9.4 | — | ns | $V_{DD} = -6.0V$ |
| t_r | Rise Time | — | 9.8 | — | | $I_D = -1.0A$ |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 240 | — | | $R_D = 6.0\Omega$ |
| t_f | Fall Time | — | 180 | — | | $V_{GS} = -4.5V$ ② |
| C_{iss} | Input Capacitance | — | 2020 | — | pF | $V_{GS} = 0V$ |
| C_{oss} | Output Capacitance | — | 520 | — | | $V_{DS} = -10V$ |
| C_{rss} | Reverse Transfer Capacitance | — | 330 | — | | $f = 1.0\text{MHz}$ |

Source-Drain Ratings and Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|----------|---|------|------|------|-------|--|
| I_S | Continuous Source Current (Body Diode) | — | — | -2.0 | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I_{SM} | Pulsed Source Current (Body Diode) ① | — | — | -39 | | |
| V_{SD} | Diode Forward Voltage | — | — | -1.2 | V | $T_J = 25^\circ\text{C}, I_S = -2.0A, V_{GS} = 0V$ ② |
| t_{rr} | Reverse Recovery Time | — | 36 | 54 | ns | $T_J = 25^\circ\text{C}, I_F = -2.0A$ |
| Q_{rr} | Reverse Recovery Charge | — | 28 | 42 | nC | $di/dt = -100A/\mu s$ ② |

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.

③ When mounted on 1 inch square copper board.

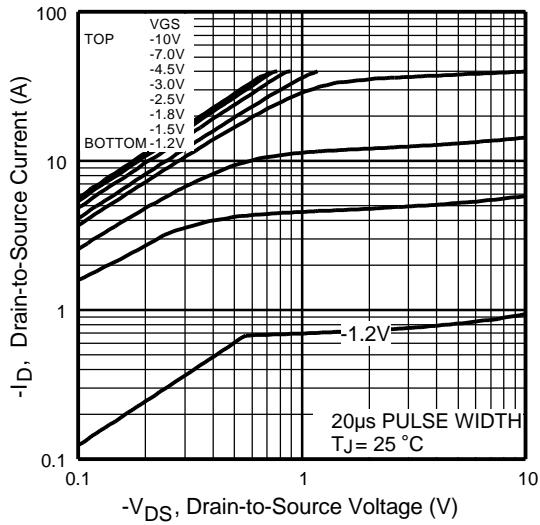


Fig 1. Typical Output Characteristics

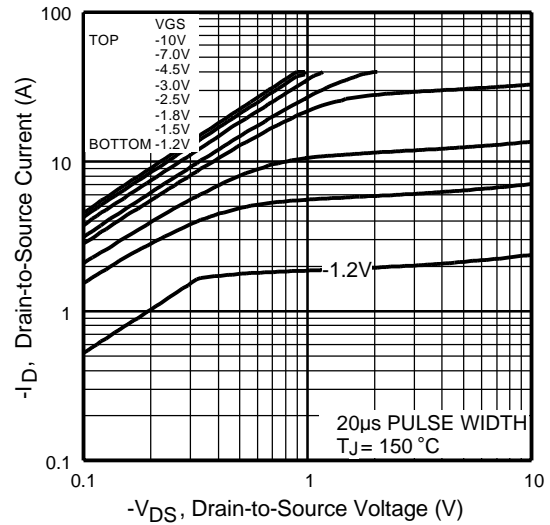


Fig 2. Typical Output Characteristics

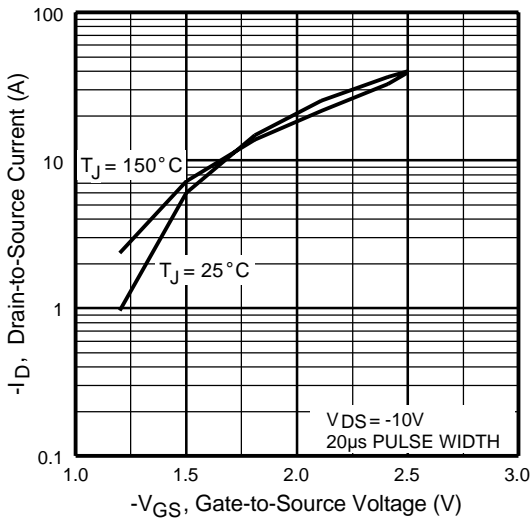


Fig 3. Typical Transfer Characteristics

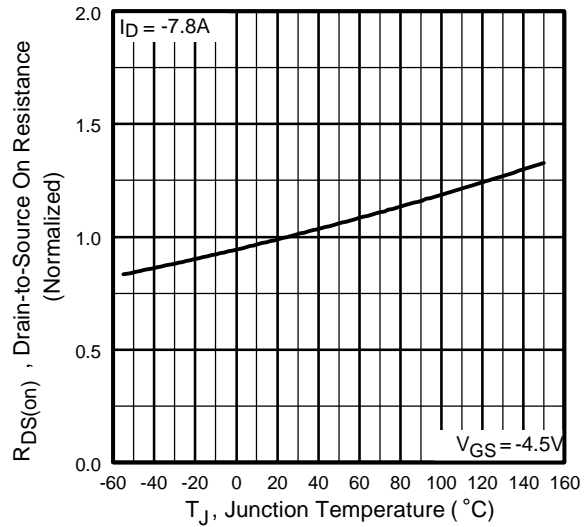


Fig 4. Normalized On-Resistance Vs. Temperature

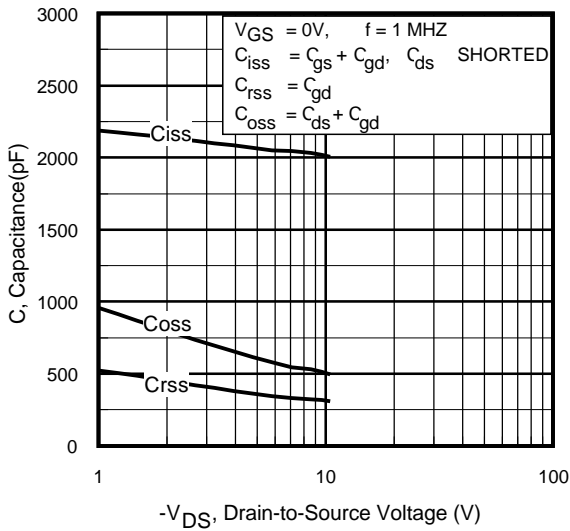


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

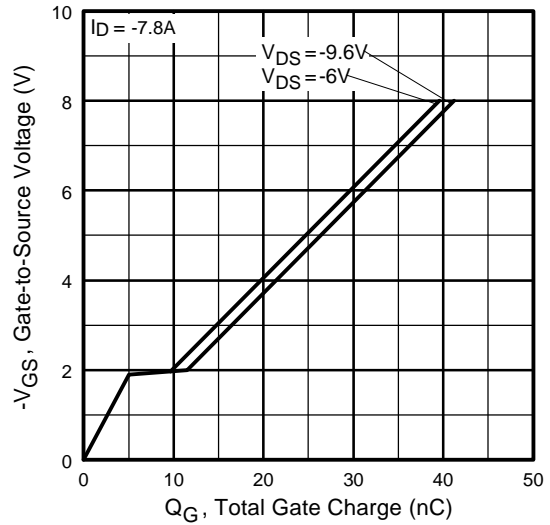


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

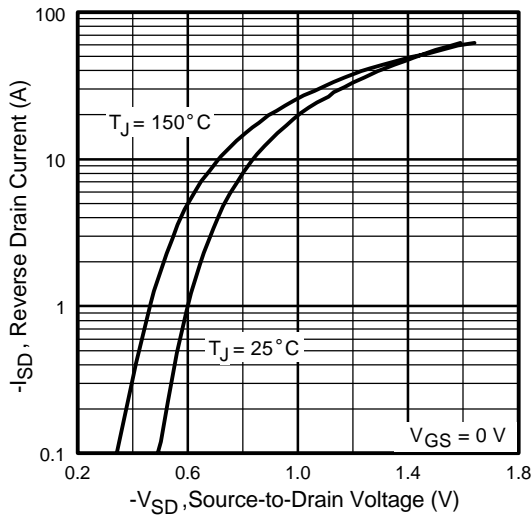


Fig 7. Typical Source-Drain Diode Forward Voltage

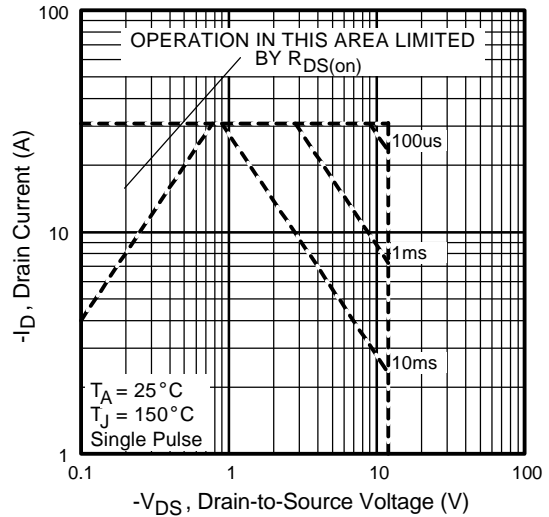


Fig 8. Maximum Safe Operating Area

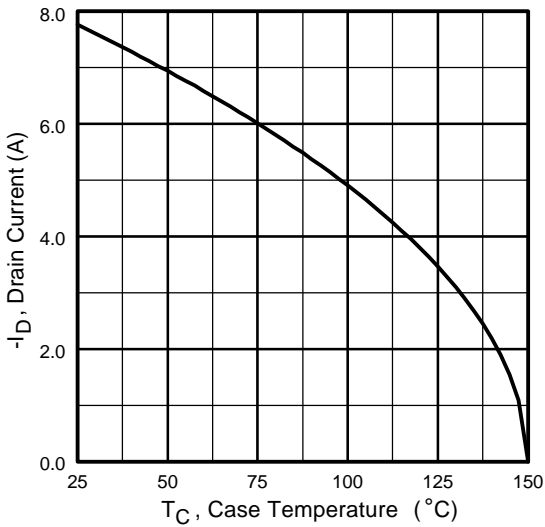


Fig 9. Maximum Drain Current Vs. Case Temperature

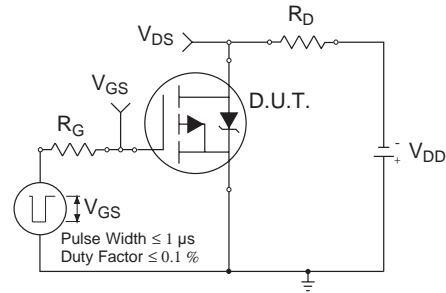


Fig 10a. Switching Time Test Circuit

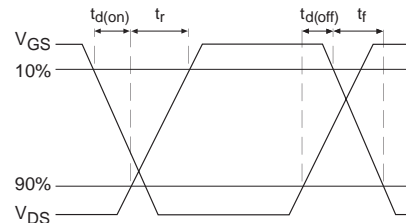


Fig 10b. Switching Time Waveforms

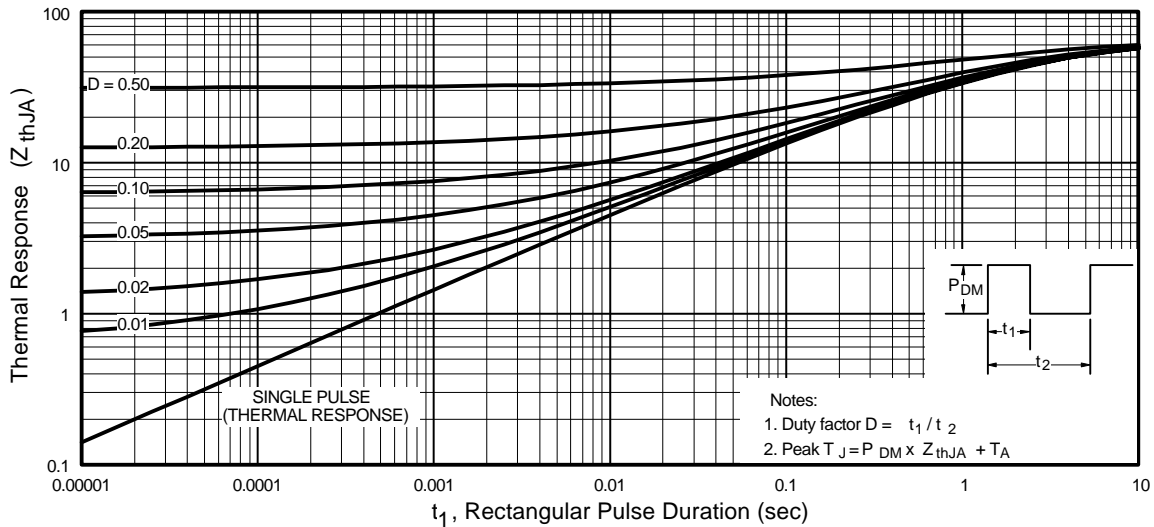


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

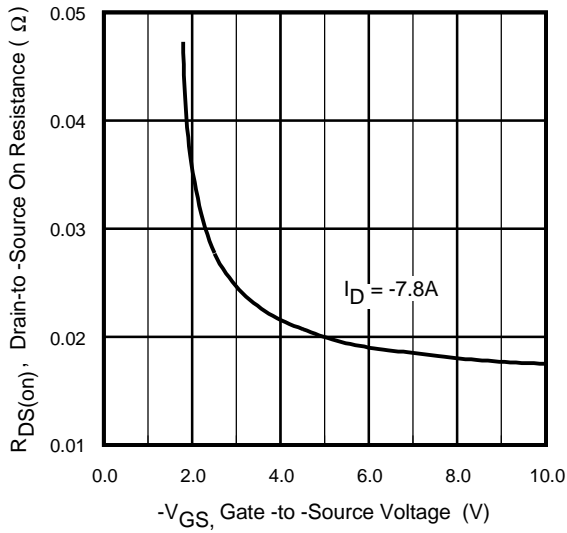


Fig 12. Typical On-Resistance Vs. Gate Voltage

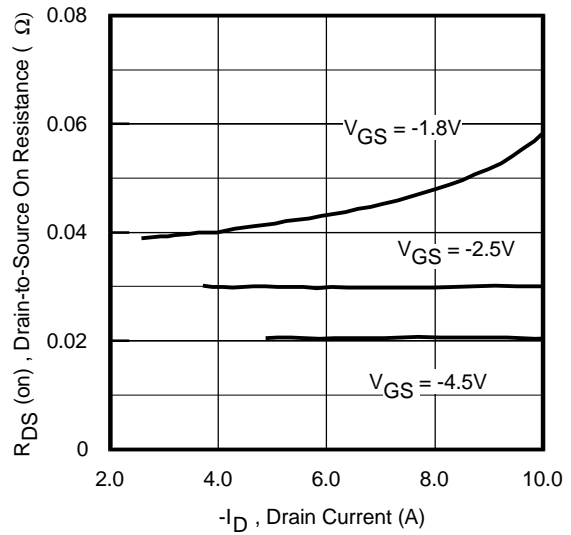


Fig 13. Typical On-Resistance Vs. Drain Current

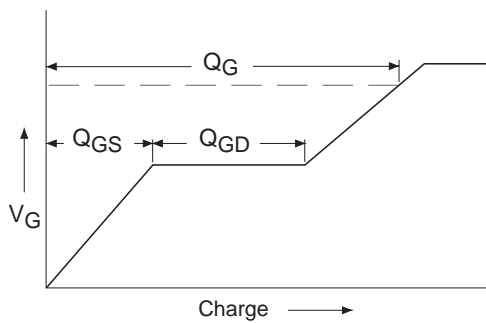


Fig 14a. Basic Gate Charge Waveform

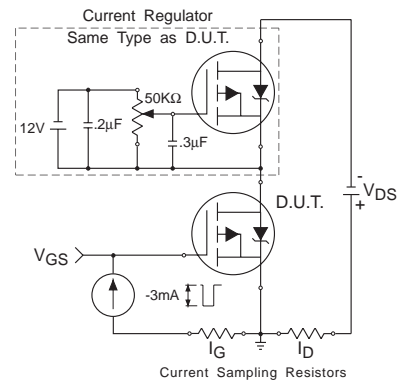


Fig 14b. Gate Charge Test Circuit

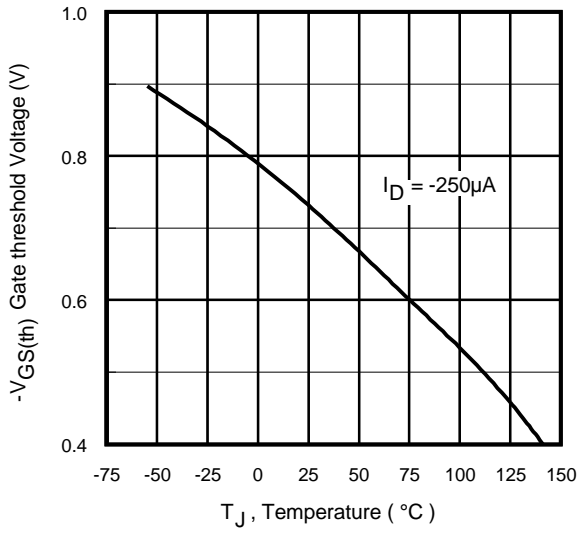


Fig 15. Typical V_{gs(th)} Vs. Junction Temperature

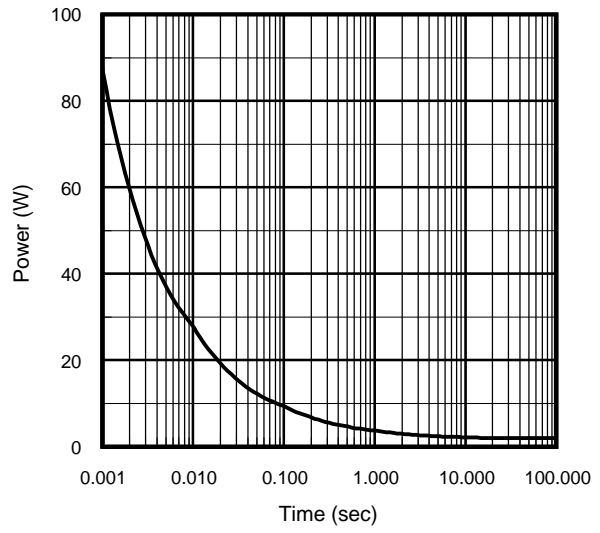
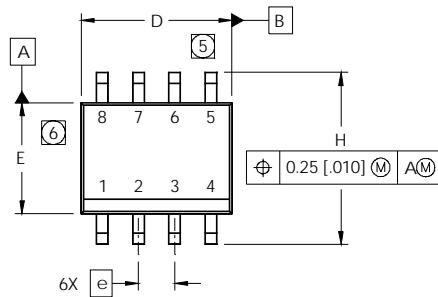


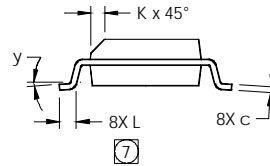
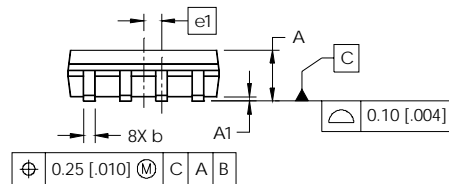
Fig 16. Typical Power Vs. Time

IRF7325

SO-8 Package Details



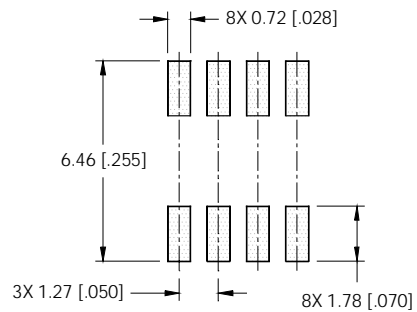
| DIM | INCHES | | MILLIMETERS | |
|-----|------------|-------|-------------|------|
| | MIN | MAX | MIN | MAX |
| A | .0532 | .0688 | 1.35 | 1.75 |
| A1 | .0040 | .0098 | 0.10 | 0.25 |
| b | .013 | .020 | 0.33 | 0.51 |
| c | .0075 | .0098 | 0.19 | 0.25 |
| D | .189 | .1968 | 4.80 | 5.00 |
| E | .1497 | .1574 | 3.80 | 4.00 |
| e | .050 BASIC | | 1.27 BASIC | |
| e1 | .025 BASIC | | 0.635 BASIC | |
| H | .2284 | .2440 | 5.80 | 6.20 |
| K | .0099 | .0196 | 0.25 | 0.50 |
| L | .016 | .050 | 0.40 | 1.27 |
| y | 0° | 8° | 0° | 8° |



NOTES:

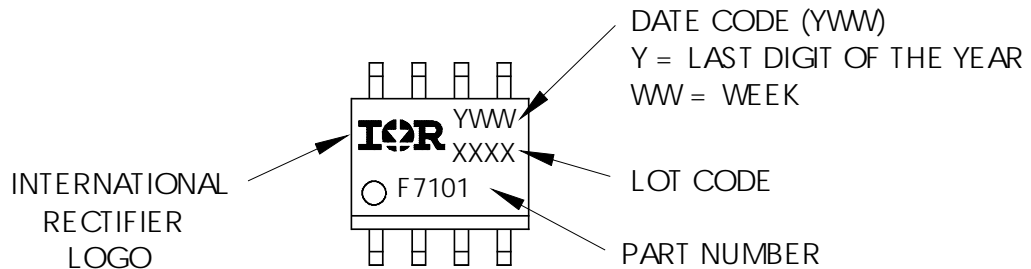
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT

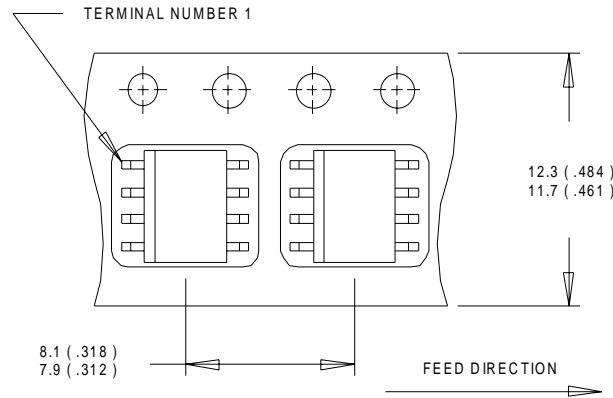


SO-8 Part Marking

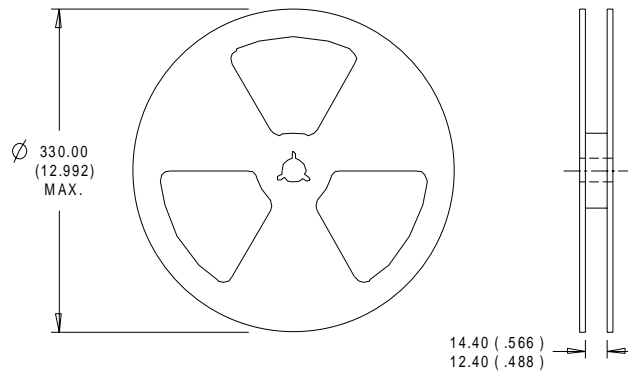
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the consumer market.
 Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
 TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information. 2/01